

# NE5550979A

R09DS0031EJ0300

Rev.3.00

## Silicon Power LDMOS FET

Mar 12, 2013

### FEATURES

- High Output Power :  $P_{out} = 39.5$  dBm TYP. ( $V_{DS} = 7.5$  V,  $I_{Dset} = 200$  mA,  $f = 460$  MHz,  $P_{in} = 25$  dBm)
- High power added efficiency :  $\eta_{add} = 66\%$  TYP. ( $V_{DS} = 7.5$  V,  $I_{Dset} = 200$  mA,  $f = 460$  MHz,  $P_{in} = 25$  dBm)
- High Linear gain :  $G_L = 22$  dB TYP. ( $V_{DS} = 7.5$  V,  $I_{Dset} = 200$  mA,  $f = 460$  MHz,  $P_{in} = 10$  dBm)
- High ESD tolerance : ESD tolerance  $> 8$  kV (IEC61000-4-2, Contact discharge)
- Suitable for VHF to UHF-BAND Class-AB power amplifier.

### APPLICATIONS

- 150 MHz Band Radio System
- 460 MHz Band Radio System
- 900 MHz Band Radio System

### ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
NE5550979A	NE5550979A-A	79A (Pb Free)	W6	<ul style="list-style-type: none"> <li>• 12 mm wide embossed taping</li> <li>• Gate pin faces the perforation side of the tape</li> </ul>
NE5550979A-T1	NE5550979A-T1-A			<ul style="list-style-type: none"> <li>• 12 mm wide embossed taping</li> <li>• Gate pin faces the perforation side of the tape</li> <li>• Qty 1 kpcs/reel</li> </ul>
NE5550979A-T1A	NE5550979A-T1A-A			<ul style="list-style-type: none"> <li>• 12 mm wide embossed taping</li> <li>• Gate pin faces the perforation side of the tape</li> <li>• Qty 5 kpcs/reel</li> </ul>

**Remark** To order evaluation samples, please contact your nearby sales office.

Part number for sample order: NE5550979A

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

Operation in excess of any one of these parameters may result in permanent damage.

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	$V_{DS}$	30	V
Gate to Source Voltage	$V_{GS}$	6.0	V
Drain Current	$I_{DS}$	3.0	A
Total Power Dissipation <sup>Note</sup>	$P_{tot}$	25	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note: Value at  $T_C = 25^\circ\text{C}$

### CAUTION

Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The mark <R> shows major revised points.

The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

**RECOMMENDED OPERATING RANGE (T<sub>A</sub> = 25°C)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V <sub>DS</sub>		–	7.5	9.0	V
Gate to Source Voltage	V <sub>GS</sub>		1.65	2.20	2.85	V
Drain Current	I <sub>DS</sub>		–	1.7	–	A
Input Power	P <sub>in</sub>	f = 460 MHz, V <sub>DS</sub> = 7.5 V	–	25	30	dBm

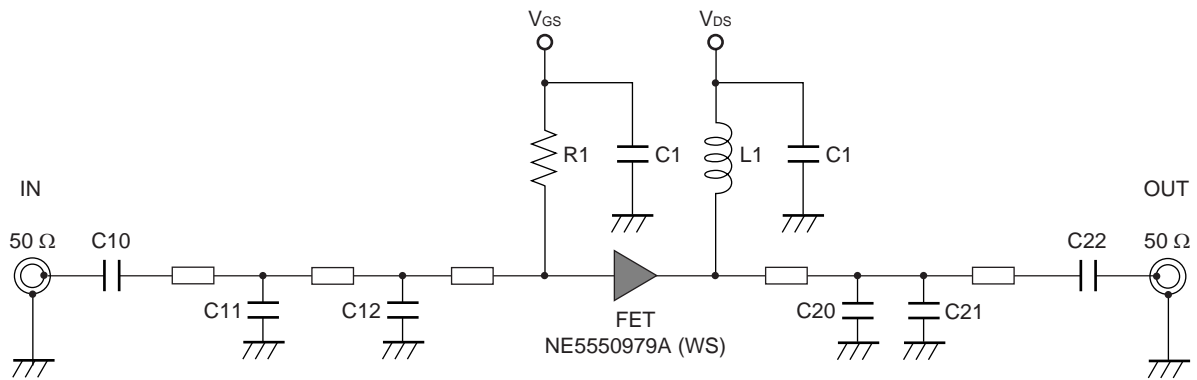
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise specified)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
<b>DC Characteristics</b>						
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = 6.0 V	–	–	100	nA
Drain to Source Leakage Current (Zero Gate Voltage Drain Current)	I <sub>DSS</sub>	V <sub>DS</sub> = 25 V	–	–	10	μA
Gate Threshold Voltage	V <sub>th</sub>	V <sub>DS</sub> = 7.5 V, I <sub>DS</sub> = 1.0 mA	1.15	1.65	2.25	V
Drain to Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>DS</sub> = 10 μA	25	37	–	V
Transconductance	G <sub>m</sub>	V <sub>DS</sub> = 7.5 V, I <sub>DS</sub> = 700±100 mA	1.8	2.2	2.9	S
Thermal Resistance	R <sub>th</sub>	Channel to Case	–	5.0	–	°C/W
<b>RF Characteristics</b>						
Output Power	P <sub>out</sub>	f = 460 MHz, V <sub>DS</sub> = 7.5 V,	38.5	39.5	–	dBm
Drain Current	I <sub>DS</sub>	P <sub>in</sub> = 25 dBm,	–	1.70	–	A
Power Drain Efficiency	η <sub>d</sub>	I <sub>Dset</sub> = 200 mA (RF OFF)	–	68	–	%
Power Added Efficiency	η <sub>add</sub>		–	66	–	%
Linear Gain	G <sub>L</sub> <sup>Note 1</sup>		–	22.0	–	dB
Output Power	P <sub>out</sub>	f = 157 MHz, V <sub>DS</sub> = 7.5 V,	–	39.6	–	dBm
Drain Current	I <sub>DS</sub>	P <sub>in</sub> = 23 dBm,	–	1.60	–	A
Power Drain Efficiency	η <sub>d</sub>	I <sub>Dset</sub> = 200 mA (RF OFF)	–	75	–	%
Power Added Efficiency	η <sub>add</sub>		–	73	–	%
Linear Gain	G <sub>L</sub> <sup>Note 2</sup>		–	25.0	–	dB
Output Power	P <sub>out</sub>	f = 900 MHz, V <sub>DS</sub> = 7.5 V,	–	38.6	–	dBm
Drain Current	I <sub>DS</sub>	P <sub>in</sub> = 27 dBm,	–	1.76	–	A
Power Drain Efficiency	η <sub>d</sub>	I <sub>Dset</sub> = 200 mA (RF OFF)	–	55	–	%
Power Added Efficiency	η <sub>add</sub>		–	52	–	%
Linear Gain	G <sub>L</sub> <sup>Note 1</sup>		–	16.0	–	dB

Note 1 : P<sub>in</sub> = 10 dBmNote 2 : P<sub>in</sub> = 5 dBm**Remark** DC performance is 100% testing. RF performance is testing several samples per wafer.

Wafer rejection criteria for standard devices is 1 reject for several samples.

TEST CIRCUIT SCHEMATIC FOR 460 MHz

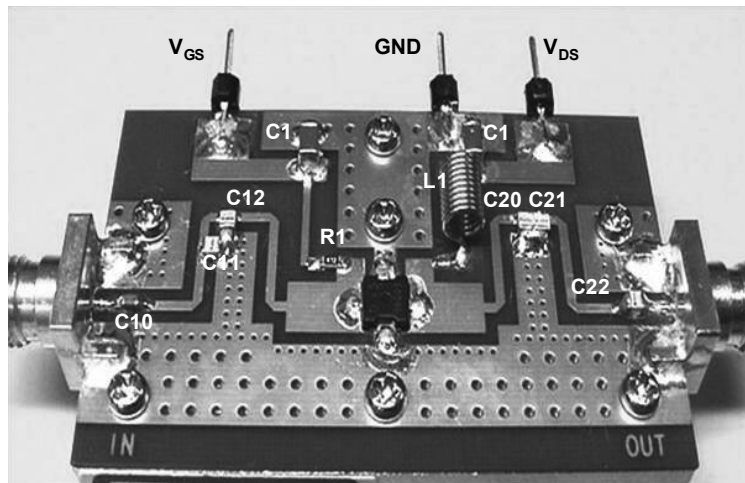


COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

Symbol	Value	Type	Maker
C1	1 $\mu$ F	GRM31CR72A105KA01B	Murata
C10	100 pF	GRM1882C1H101JA01	Murata
C11	24 pF	ATC100A240JW	American Technical Ceramics
C12	2.4 pF	ATC100A2R4BW	American Technical Ceramics
C20	27 pF	ATC100A270JW	American Technical Ceramics
C21	1.8 pF	ATC100A1R8BW	American Technical Ceramics
C22	100 pF	ATC100A101JW	American Technical Ceramics
R1	4.7 k $\Omega$	1/10 W Chip Resistor SSM_RG1608PB472	SSM
L1	123 nH	$\phi$ 0.5 mm, $\phi$ D = 3 mm, 10 Turns	Ohesangyou
PCB	-	R1766, t = 0.4 mm, $\epsilon$ r = 4.5, size = 30 $\times$ 48 mm	Panasonic
SMA Connector	-	WAKA 01K0790-20	WAKA

<R>

COMPONENT LAYOUT OF TEST CIRCUIT FOR 460 MHz

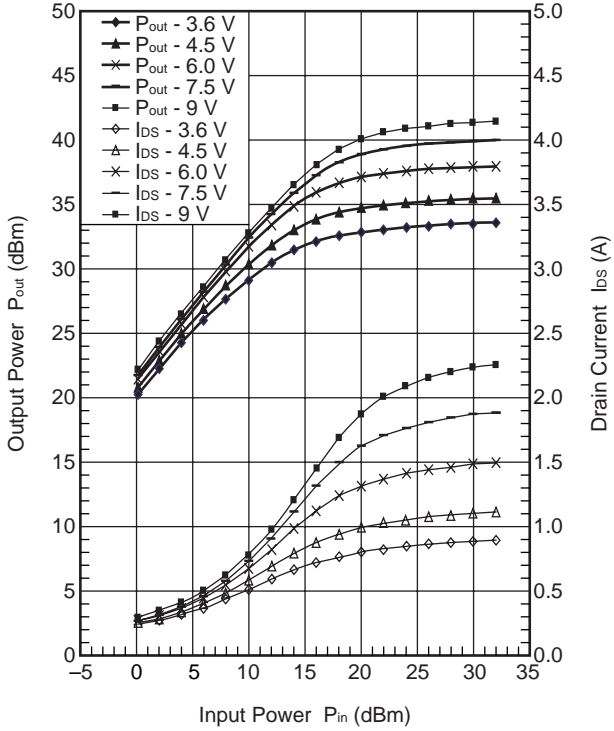


**TYPICAL CHARACTERISTICS 1 (T<sub>A</sub> = 25°C)**

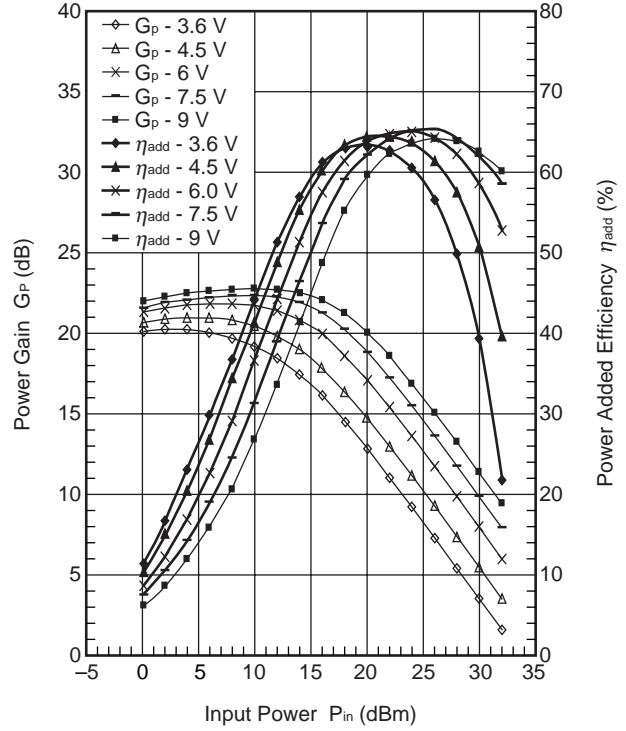
**R:** f = 460MHz, V<sub>DS</sub> = 3.6/4.5/6/7.5/8.4/9 V, I<sub>Dset</sub> = 200 mA, P<sub>in</sub> = 0 to 32 dBm

**IM:** f1 = 460MHz, f2 = 461 MHz, V<sub>DS</sub> = 3.6/4.5/6/7.5/8.4/9 V, I<sub>Dset</sub> = 200mA, P<sub>out</sub> (2 tone) = 12 to 38 dBm

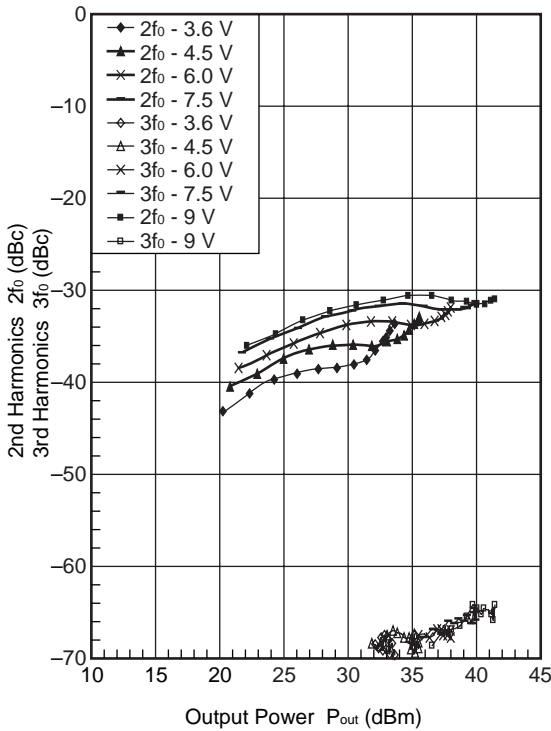
OUTPUT POWER, DRAIN CURRENT vs. INPUT POWER



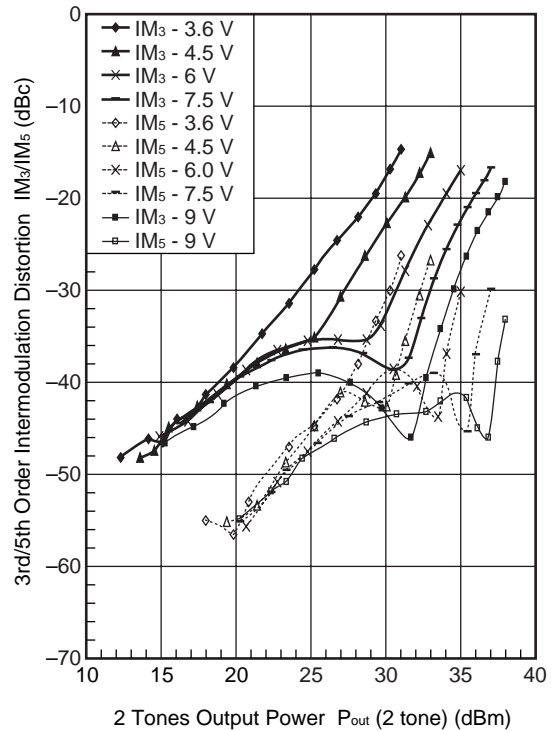
POWER GAIN, POWER ADDED EFFICIENCY vs. INPUT POWER



2f<sub>0</sub>, 3f<sub>0</sub> vs. OUTPUT POWER

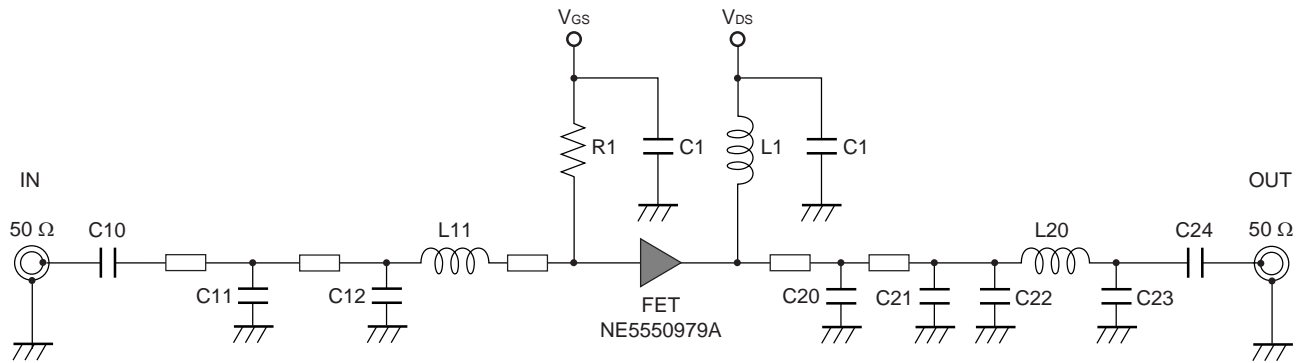


IM<sub>3</sub>/IM<sub>5</sub> vs. 2 TONES OUTPUT POWER



**Remark** The graphs indicate nominal characteristics.

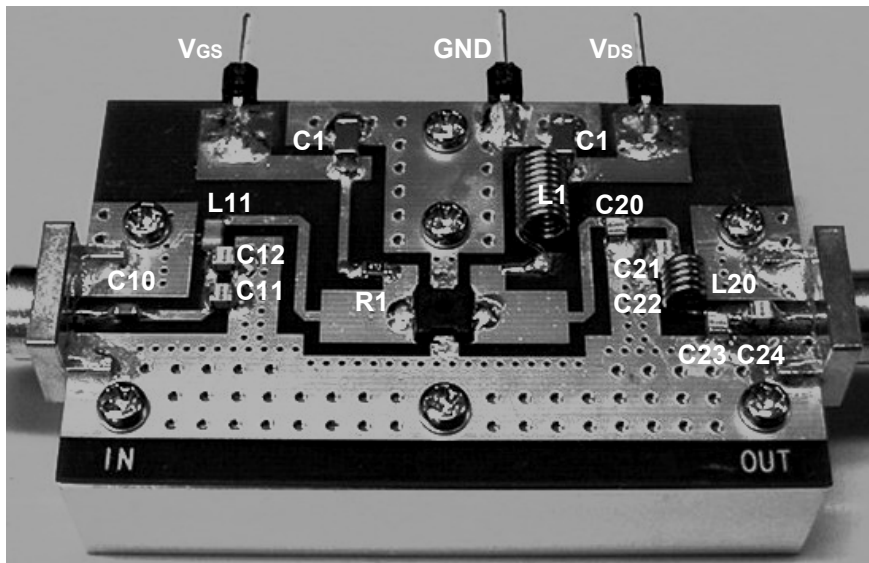
## &lt;R&gt; TEST CIRCUIT SCHEMATIC FOR 157 MHz



## &lt;R&gt; COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

Symbol	Value	Type	Maker
C1	1 $\mu$ F	GRM31CR72A105KA01B	Murata
C10	100 pF	GRM1882C1H101JA01	Murata
C11	4.7 pF	ATC100A4R7CT	American Technical Ceramics
C12	39 pF	ATC100A390JT	American Technical Ceramics
C20	2.0 pF	ATC100A2R0CT	American Technical Ceramics
C21	22 pF	ATC100A220JT	American Technical Ceramics
C22	68 pF	ATC100A680JT	American Technical Ceramics
C23	12 pF	ATC100A120JT	American Technical Ceramics
C24	100 pF	ATC100A101JT	American Technical Ceramics
R1	4.7 k $\Omega$	1/10 W Chip Resistor SSM_RG1608PB472	SSM
L1	123 nH	$\phi$ 0.5 mm, $\phi$ D = 3 mm, 10 Turns	Ohesangyou
L11	27 nH	LLQ2012-F27N	TOKO
L20	35 nH	$\phi$ 0.5 mm, $\phi$ D = 2.4 mm, 5 Turns	Ohesangyou
PCB	-	R1766, t = 0.4 mm, $\epsilon$ = 4.5, size = 30 $\times$ 48 mm	Panasonic
SMA Connector	-	WAKA 01K0790-20	WAKA

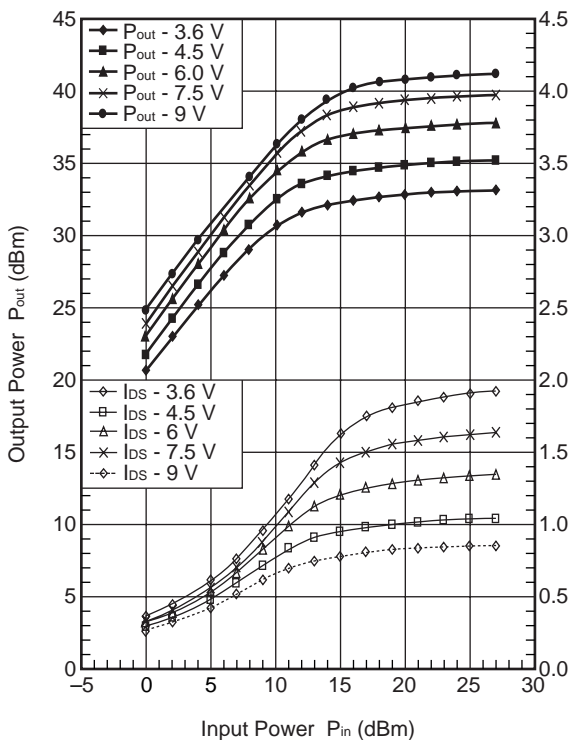
COMPONENT LAYOUT OF TEST CIRCUIT FOR 157 MHz



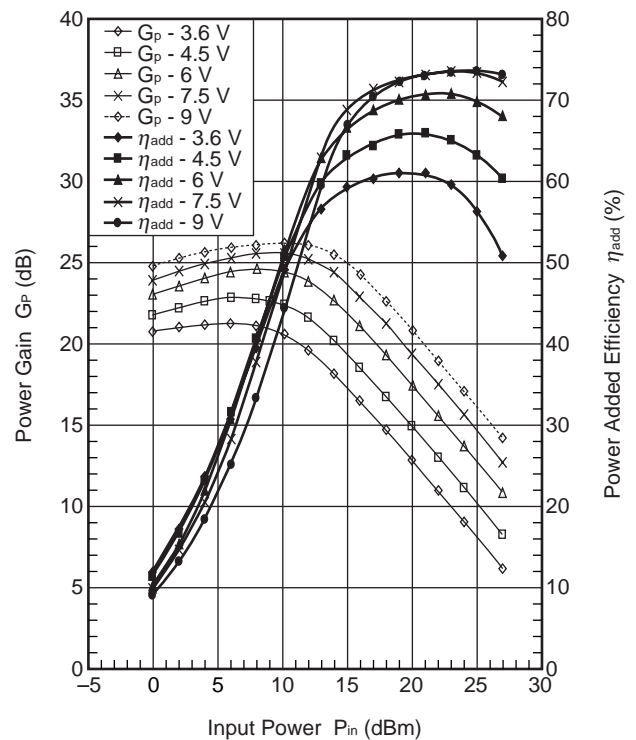
TYPICAL CHARACTERISTICS 2 ( $T_A = 25^\circ\text{C}$ )

R:  $f = 157 \text{ MHz}$ ,  $V_{DS} = 3.6/4.5/6/7.5/9 \text{ V}$ ,  $I_{Dset} = 200 \text{ mA}$ ,  $P_{in} = 0 \text{ to } 27 \text{ dBm}$

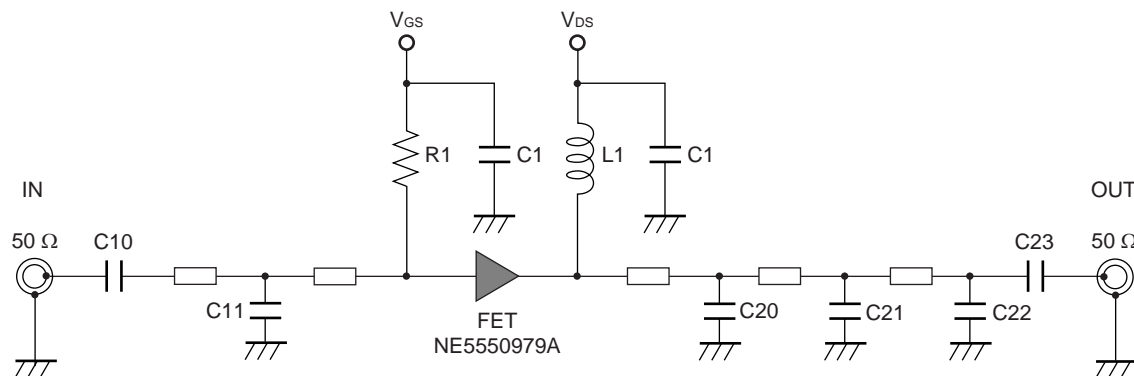
OUTPUT POWER, DRAIN CURRENT vs. INPUT POWER



POWER GAIN, POWER ADDED EFFICIENCY vs. INPUT POWER



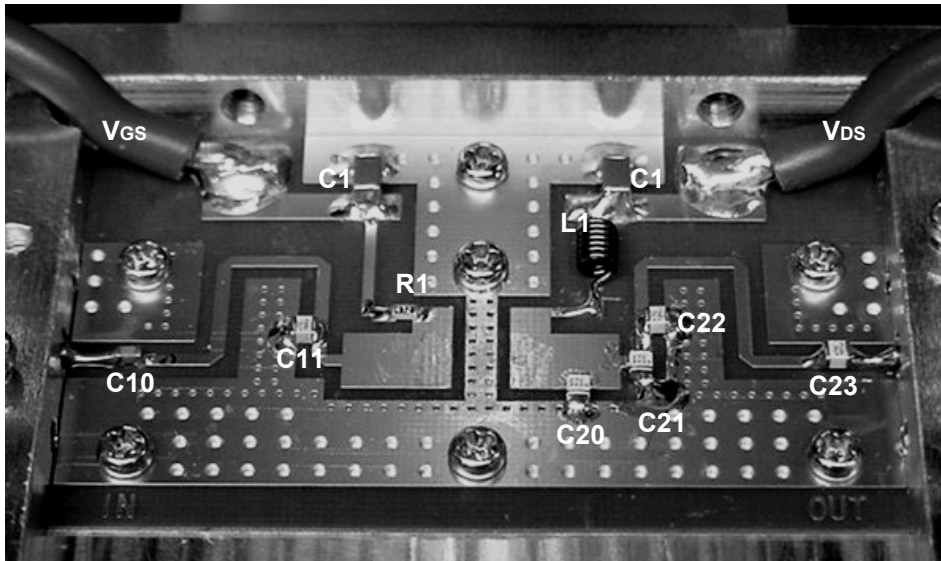
## TEST CIRCUIT SCHEMATIC FOR 900 MHz



## &lt;R&gt; COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

Symbol	Value	Type	Maker
C1	1 $\mu$ F	GRM31CR72A105KA01B	Murata
C10	100 pF	GRM1882C1H101JA01	Murata
C11	15 pF	ATC100A150JW	American Technical Ceramics
C20	3.3 pF	ATC100A3R3BW	American Technical Ceramics
C21	3.3 pF	ATC100A3R3BW	American Technical Ceramics
C22	12 pF	ATC100A120JT	American Technical Ceramics
C23	100 pF	ATC100A101JT	American Technical Ceramics
R1	4.7 k $\Omega$	1/10 W Chip Resistor SSM_RG1608PB472	SSM
L1	123 nH	$\phi$ 0.5 mm, $\phi$ D = 3 mm, 10 Turns	Ohesangyou
PCB	-	R1766, t = 0.4 mm, $\epsilon$ = 4.5, size = 30 $\times$ 48 mm	Panasonic
SMA Connector	-	WAKA 01K0790-20	WAKA

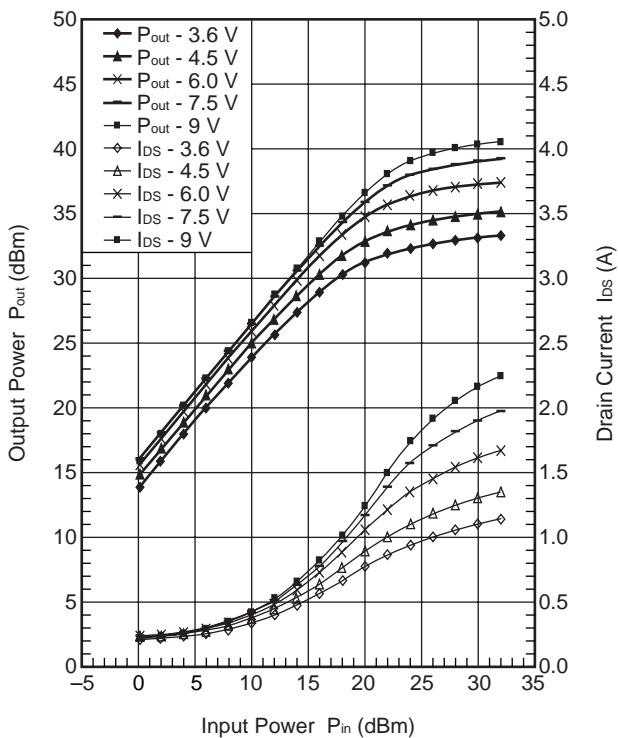
COMPONENT LAYOUT OF TEST CIRCUIT FOR 900 MHz



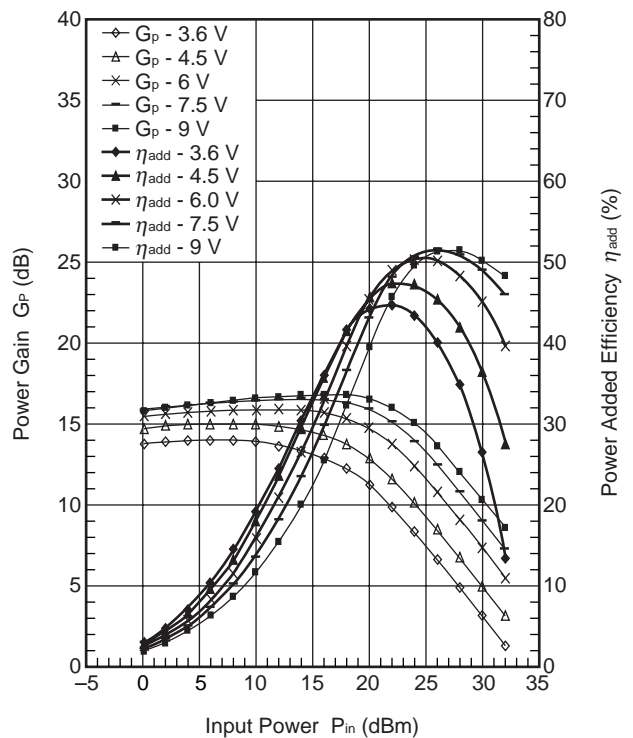
TYPICAL CHARACTERISTICS 3 (T<sub>A</sub> = 25°C)

RF: f = 900 MHz V<sub>DS</sub> = 3.6/4.5/6/7.5/9 V, I<sub>Dset</sub> = 200 mA, P<sub>in</sub> = 0 to 32 dBm

OUTPUT POWER, DRAIN CURRENT vs. INPUT POWER



POWER GAIN, POWER ADDED EFFICIENCY vs. INPUT POWER



**Remark** The graphs indicate nominal characteristics.



## S-PARAMETERS

S-parameters and noise parameters are provided on our web site in a form (S2P) that enables direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

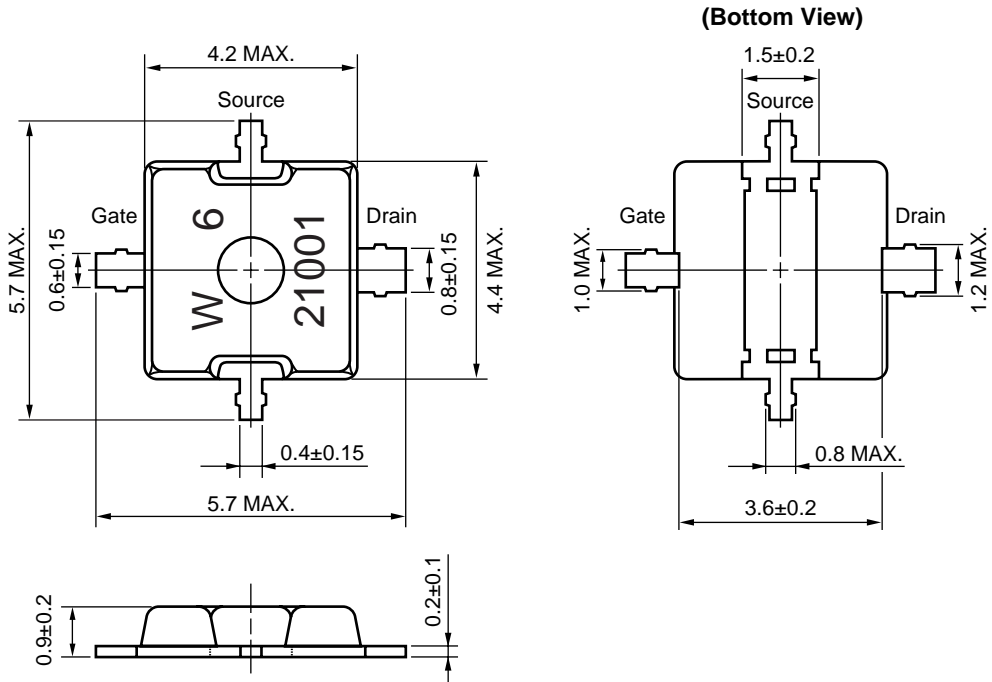
Click here to download S-parameters.

[Products] → [RF Devices] → [Device Parameters]

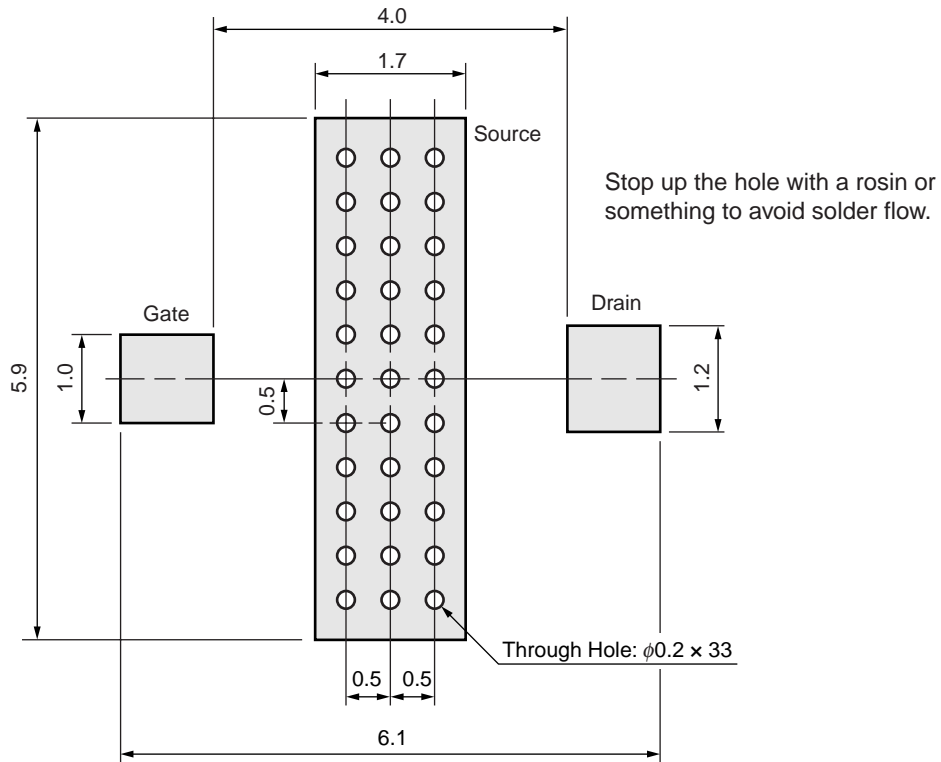
URL <http://www.renesas.com/products/microwave/>

**PACKAGE DIMENSIONS**

79A (UNIT: mm)



**79A PACKAGE RECOMMENDED P.C.B. LAYOUT (UNIT: mm)**



**RECOMMENDED SOLDERING CONDITIONS**

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

<b>Soldering Method</b>	<b>Soldering Conditions</b>	<b>Condition Symbol</b>
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2% (Wt.) or below	IR260
Wave Soldering	Peak temperature (molten solder temperature) : 260°C or below Time at peak temperature : 10 seconds or less Preheating temperature (package surface temperature) : 120°C or below Maximum number of flow processes : 1 time Maximum chlorine content of rosin flux (% mass) : 0.2% (Wt.) or below	WS260
Partial Heating	Peak temperature (terminal temperature) : 350°C or below Soldering time (per side of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2% (Wt.) or below	HS350

**CAUTION**

Do not use different soldering methods together (except for partial heating).

**Revision History****NE5550979A Data Sheet**

Rev.	Date	Description	
		Page	Summary
1.00	Nov 25, 2011	–	First edition issued
2.00	Jul 04, 2012	p.1	Modification of ORDERING INFORMATION
		p.5	Addition of TEST CIRCUIT SCHEMATIC FOR 157 MHz
		p.6	Addition of COMPONENT LAYOUT OF TEST CIRCUIT FOR 157 MHz
		p.7	Addition of TEST CIRCUIT SCHEMATIC FOR 900 MHz
		p.8	Addition of COMPONENT LAYOUT OF TEST CIRCUIT FOR 900 MHz
		p.9	Modification of S-PARAMETERS
3.00	Mar 12, 2013	P3	Modification of COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS
		P5	Modification of TEST CIRCUIT SCHEMATIC FOR 157 MHz
			Modification of COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS
P7	Modification of COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS		

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